

GEN2 SiC Schottky Diode LSIC2SD120D20, 1200 V, 20 A, TO-263-2L

LSIC2SD120D20









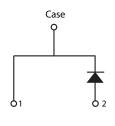
Description

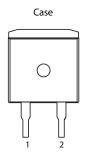
This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- · Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-263-2L





Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = Po Pb-free lead plating

Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	1200	V	
DC Blocking Voltage	V _R	T _J = 25 °C	1200	V	
		T _C = 25 °C	54.5		
Continuous Forward Current	I _F	T _C = 135 °C	26.0	А	
		T _C = 150 °C	20.0		
Non-Repetitive Forward Surge Current	I _{FSM}	$T_{\rm C}$ = 25 °C, $T_{\rm p}$ = 10 ms, Half sine pulse	140	А	
Power Dissipation	В	T _C = 25 °C	250	W	
rower dissipation	P _{Tot}	T _C = 110 °C	108		
Operating Junction Temperature	T	-	-55 to 175	°C	
Storage Temperature	T _{STG}	-	-55 to 150	°C	
Soldering Temperature (reflow MSL1)	T _{sold}	-	260	°C	

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Electrical Characteristics

			Value			
Characteristics	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Voltage V _F	\/	I _F = 20 A, T _J = 25 °C	-	1.5	1.8	V
	V _F	I _F = 20 A, T _J = 175 °C	-	2.2	-	
Reverse Current		$V_{_{\rm R}} = 1200 \text{V}, T_{_{\rm J}} = 25 ^{\circ}\text{C}$	-	<1	100	μΑ
	I _R	$V_{R} = 1200 V$, $T_{J} = 175 ^{\circ}C$	-	15		
		$V_R = 1 V$, $f = 1 MHz$	-	1142	-	
Total Capacitance C	С	$V_R = 400 \text{ V, f} = 1 \text{ MHz}$	-	108	-	pF
		V _R = 800 V, f = 1 MHz	-	82	-	
Total Capacitive Charge	Q _c	$V_R = 800 \text{ V}, Q_C = \int\limits_0^{V_R} C(V) dV$	-	115	-	nC

Footnote: T₁ = +25 °C unless otherwise specified

Thermal Characteristics

Characteristics Symbo		Symbol Conditions	Value			
	Symbol		Min.	Тур.	Max.	Unit
Thermal Resistance	R	-	-	0.6	-	°C/W

Figure 1: Typical Foward Characteristics

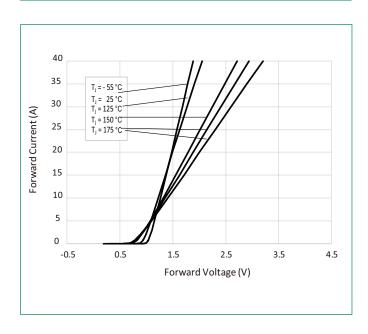


Figure 2: Typical Reverse Characteristics

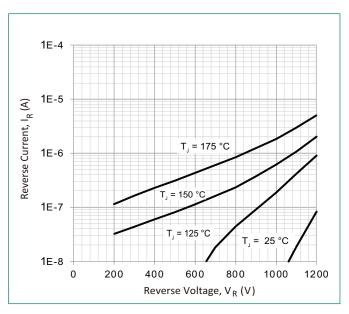




Figure 3: Power Derating

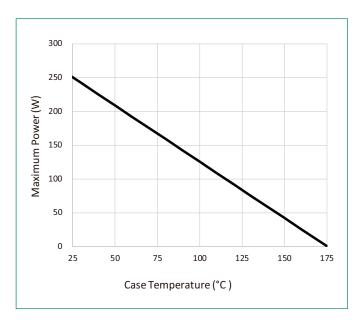


Figure 4: Current Derating

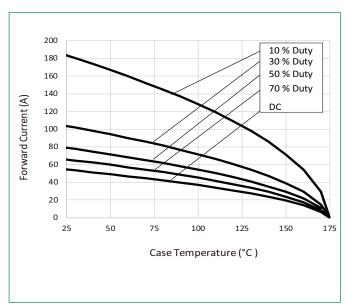


Figure 5: Capacitance vs. Reverse Voltage

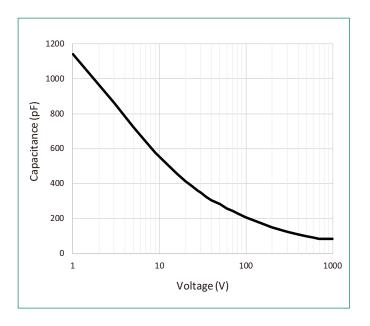


Figure 6: Capacitive Charge vs. Reverse Voltage

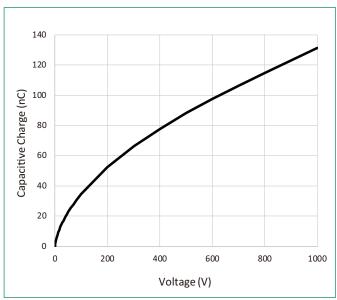




Figure 7: Stored Energy vs. Reverse Voltage

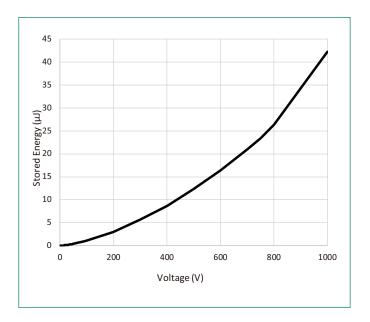
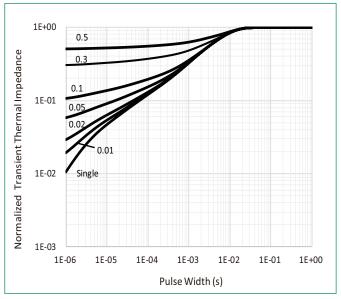
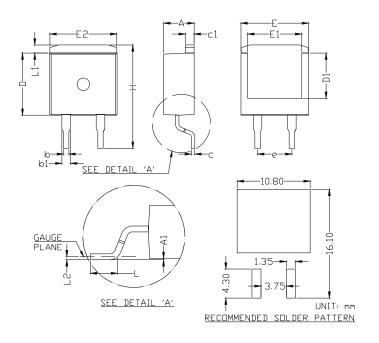


Figure 8: Transient Thermal Impedance



Dimensions-Package TO-263-2L

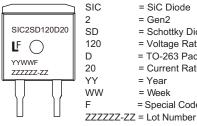


Symbol	Millimeters				
	Min	Nom	Max		
А	4.30	4.50	4.70		
A1	0.00	-	0.25		
b	0.70	0.80	0.90		
b1	1.17	1.27	1.37		
С	0.46	0.50	0.60		
c1	1.25	1.30	1.40		
D	9.00	9.20	9.40		
D1	6.50	6.70	6.90		
Е	9.80	10.00	10.20		
E1	7.80	8.00	8.20		
E2	9.70	9.90	10.10		
е	5.08 BSC				
Н	15.00	15.30	15.60		
L	2.00	2.30	2.60		
L1	1.00	1.20	1.40		
L2	0.254 BSC				



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Part Numbering and Marking System



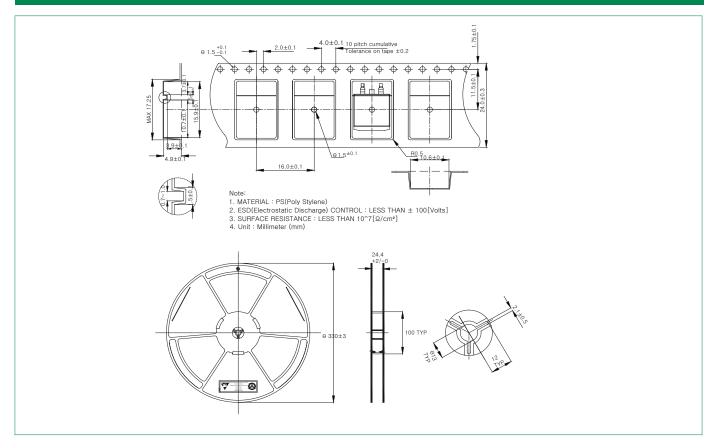
SIC = SiC Diode = Gen2 = Schottky Diode 120 = Voltage Rating (1200 V) = TO-263 Package (2 Lead) = Current Rating (20 A) = Year = Week

= Special Code

Packing Option

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD120D20	SIC2SD120D20	Tape and Reel	800

TO-263 Carrier Reel Specifications



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